

MATERIALS SCIENCE

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# Metal Impurities in Silicon-Device Fabrication

Second, Revised Edition

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# Contents

1. Introduction . . . . .	1
2. Common Properties of Transition Metals . . . . .	5
2.1 General Behavior . . . . .	5
2.2 Contamination of Silicon Wafers . . . . .	9
2.2.1 Solid Phase . . . . .	9
2.2.2 Liquid Phase . . . . .	10
2.2.3 Vapor Phase . . . . .	12
2.3 Impact on Device Performance . . . . .	14
2.3.1 Dissolved Transition Metals . . . . .	15
2.3.2 Precipitated Transition Metals . . . . .	18
3. Properties of Transition Metals in Silicon . . . . .	20
3.1 Solubilities . . . . .	21
3.2 Diffusivities . . . . .	25
3.3 Dissolved Impurities . . . . .	30
3.3.1 Point Defects . . . . .	32
3.3.2 Complexes . . . . .	42
3.4 Precipitated Metals . . . . .	51
3.4.1 Volume Precipitates . . . . .	52
3.4.2 Surface Precipitates - Haze . . . . .	58
3.4.3 Haze Phenomena . . . . .	63
4. Properties of the Main Impurities . . . . .	76
4.1 Iron . . . . .	77
4.1.1 Solubility . . . . .	77
4.1.2 Diffusivity . . . . .	78
4.1.3 Behavior During Heat Treatment . . . . .	79
4.1.4 Electrical Activity . . . . .	80
4.1.5 Properties of the Precipitates . . . . .	86
4.1.6 Known Impurity Sources, and Common Concentrations . . . . .	87
4.1.7 Avoidance of Contamination . . . . .	88
4.2 Nickel . . . . .	89
4.2.1 Solubility . . . . .	90
4.2.2 Diffusivity . . . . .	91
4.2.3 Behavior During Heat Treatment . . . . .	92
4.2.4 Electrical Activity . . . . .	93
4.2.5 Properties of the Precipitates . . . . .	95

4.2.6	Known Impurity Sources, and Common Concentrations	96
4.2.7	Avoidance of Contamination	97
4.3	Copper	98
4.3.1	Solubility	99
4.3.2	Diffusivity	99
4.3.3	Behavior During Heat Treatment	100
4.3.4	Electrical Activity	101
4.3.5	Properties of the Precipitates	103
4.3.6	Known Impurity Sources and Common Concentrations	104
4.3.7	Avoidance of Contamination	105
4.4	Molybdenum	106
4.4.1	Solubility	107
4.4.2	Diffusivity	107
4.4.3	Behavior During Heat Treatment	108
4.4.4	Electrical Activity	108
4.4.5	Properties of the Precipitates	108
4.4.6	Known Impurity Sources and Common Concentrations	108
4.4.7	Avoidance of Contamination	109
4.5	Palladium	109
4.5.1	Solubility	110
4.5.2	Diffusivity	111
4.5.3	Behavior During Heat Treatment	112
4.5.4	Electrical Activity	113
4.5.5	Properties of the Precipitates	115
4.5.6	Known Impurity Sources and Common Concentrations	117
4.6	Platinum	117
4.6.1	Solubility	118
4.6.2	Diffusivity	119
4.6.3	Behavior During Heat Treatment	120
4.6.4	Electrical Activity	121
4.6.5	Properties of the Precipitates	123
4.6.6	Known Impurity Sources and Common Concentrations	123
4.6.7	Avoidance of Contamination	123
4.7	Gold	124
4.7.1	Solubility	125
4.7.2	Diffusivity	125
4.7.3	Behavior During Heat Treatment	126
4.7.4	Electrical Activity	127
4.7.5	Properties of the Precipitates	129
4.7.6	Known Impurity Sources and Common Concentrations	129
4.7.7	Avoidance of Contamination	130



<b>5. Properties of Rare Impurities</b> . . . . .	<b>131</b>
<b><i>3d Transition Metals</i></b>	
5.1 Scandium . . . . .	132
5.2 Titanium . . . . .	134
5.3 Vanadium . . . . .	136
5.4 Chromium . . . . .	138
5.5 Manganese . . . . .	141
5.6 Cobalt . . . . .	144
5.7 Zinc . . . . .	147
<b><i>4d Transition Metals</i></b>	
5.8 Zircon . . . . .	149
5.9 Niobium . . . . .	150
5.10 Ruthenium . . . . .	151
5.11 Rhodium . . . . .	151
5.12 Silver . . . . .	153
5.13 Cadmium . . . . .	156
<b><i>5d Transition Metals</i></b>	
5.14 Hafnium . . . . .	157
5.15 Tantalum . . . . .	157
5.16 Tungsten . . . . .	158
5.17 Rhenium . . . . .	160
5.18 Osmium . . . . .	160
5.19 Iridium . . . . .	161
5.20 Mercury . . . . .	162
<b>6. Detection Methods</b> . . . . .	<b>163</b>
6.1 Detection of Total Impurity Content . . . . .	163
6.1.1 Neutron Activation Analysis . . . . .	164
6.1.2 Mass Spectrometers, Secondary Ion Mass Spectrometers . . . . .	164
6.1.3 Atomic Absorption Spectroscopy . . . . .	165
6.1.4 Vapor-Phase Decomposition . . . . .	165
6.1.5 Inductively-Coupled Plasma Spectroscopy . . . . .	166
6.1.6 Total-Reflection X-Ray Fluorescence Analysis . . . . .	166
6.2 Detection of Dissolved Impurities . . . . .	168
6.2.1 Deep Level Transient Spectroscopy . . . . .	169
6.2.2 Carrier Lifetime . . . . .	177
6.2.3 Diffusion Length . . . . .	181
6.3 Detection of Precipitates . . . . .	185
6.3.1 Haze Test . . . . .	186
<b>7. Requirements of Modern Technology</b> . . . . .	<b>190</b>
7.1 Reduction of Contamination . . . . .	192
7.1.1 Control of Ingots . . . . .	192
7.1.2 Process Control . . . . .	198

<b>8. Gettering of Impurities</b> . . . . .	201
8.1 Gettering Mechanisms . . . . .	202
8.2 Control of Gettering Efficiency . . . . .	207
8.2.1 Conventional Methods . . . . .	207
8.2.2 Palladium Test . . . . .	208
8.2.3 Iron Test . . . . .	215
<b>9. Conclusion and Future Trends</b> . . . . .	233
<b>Appendix</b> . . . . .	239
<b>References</b> . . . . .	246
<b>Subject Index</b> . . . . .	267